Advance Information 2-Input OR Gate/CMOS Logic Level Shifter

The MC74VHC1GT32 is an advanced high speed CMOS 2–input OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT32 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT32 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 3.5$ ns (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL–Compatible Inputs: $V_{IL} = 0.8 \text{ V}; V_{IH} = 2.0 \text{ V}$
- CMOS–Compatible Outputs: $V_{OH} > 0.8 V_{CC}$; $V_{OL} < 0.1 V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; MM > 200 V, CDM > 1500 V

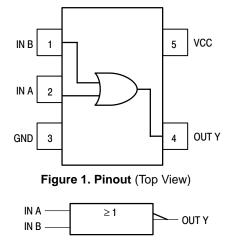


Figure 2. Logic Symbol

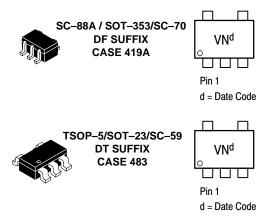
This document contains information on a new product. Specifications and information herein are subject to change without notice.



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MARKING DIAGRAMS



	PIN ASSIGNMENT
1	IN B
2	IN A
3	GND
4	OUT Y
5	VCC

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	н

Semiconductor Components Industries, LLC, 2000 August, 2000 – Rev. 0

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	V _{IN}	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	I _{OK}	+20	mA
DC Output Current, per Pin	lout	+25	mA
DC Supply Current, V _{CC} and GND	I _{CC}	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC-88A Package: -3 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Cha	racteristics	Symbol	Min	Max	Unit
DC Supply Voltage		V _{CC}	3.0	5.5	V
DC Input Voltage		V _{IN}	0.0	5.5	V
	V _{CC} = 0 High or Low State	V _{OUT}	0.0 0.0	5.5 V _{CC}	V
Operating Temperature Rang	e	T _A	-55	+125	°C
	$V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t _r , t _f	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

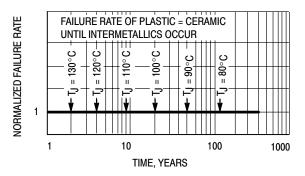


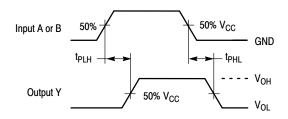
Figure 3. Failure Rate vs. Time Junction Temperature

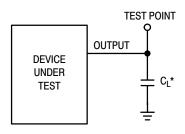
			V _{cc}	ר	Γ _A = 25°	C	TA ≤	85°C	T _A ≤ <i>′</i>	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Мах	Min	Max	Min	Мах	Unit
V _{IH}	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH} Minimum High–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu \text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V	
	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V	
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu \text{A}$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0.0			0.5		5.0		10	μΑ

DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_r = t_f = 3.0 \text{ ns}$)

Symbol Parameter			T _A = 25°C			$T_A \le 85^\circ C$		T _A ≤ 125°C			
	Parameter	Test Condi	Min	Тур	Max	Min	Max	Min	Max	Unit	
t _{PLH} , Maximum t _{PHL} Propogation Delay, Input A or B to Y	$V_{CC} = 3.0 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		4.8 6.1	7.9 11.4		9.5 13.0		11.5 15.5	ns	
	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15 pF C _L = 50 pF		3.7 4.4	5.5 7.5		6.5 8.5		8.0 10.0		
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF
					·	דַ	ypical @	25°C, V	/ _{CC} = 5.0	DV V	<u> </u>
C _{PD}	Power Dissipation Ca	pacitance (Note 1.)						11			pF





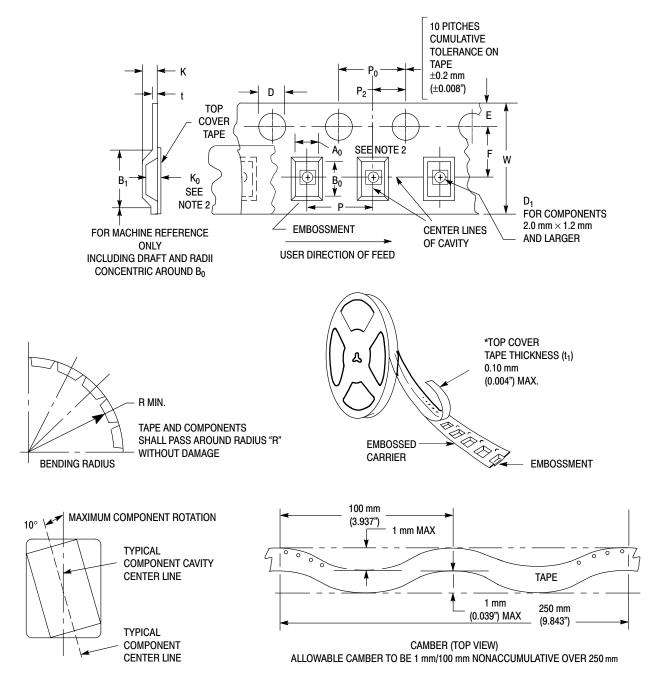
*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 4. Switching Waveforms

DEVICE ORDERING INFORMATION

			Device Nome	nclature				
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1GT32DFT2	MC	74	VHC1G	T32	DF	T2	SC-88A/ SOT-353 /SC-70	178mm (7") 3000 Unit
MC74VHC1GT32DFT4	MC	74	VHC1G	T32	DF	T4	SC-88A/ SOT-353 /SC-70	330mm (13") 100000 Unit
MC74VHC1GT32DTT1	MC	74	VHC1G	T32	DT	T1	TSOP5/ SOT–23 /SC–59	178mm (7") 3000 Unit
MC74VHC1GT32DTT3	MC	74	VHC1G	T32	DT	ТЗ	TSOP5/ SOT–23 /SC–59	330mm (13") 100000 Unit





Tape Size	B ₁ Max	D	D ₁	Е	F	к	Р	Po	P ₂	R	т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED	CARRIER	DIMENSIONS	(See	Notes	1	and 2)
LINDOOOLD	OANNEN	DIMILINGIONO	(000	110163		anu z

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

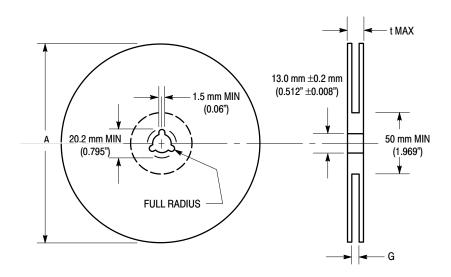


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")

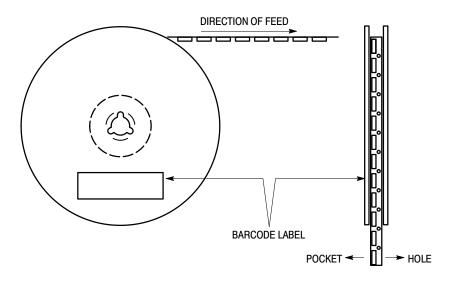


Figure 8. Reel Winding Direction

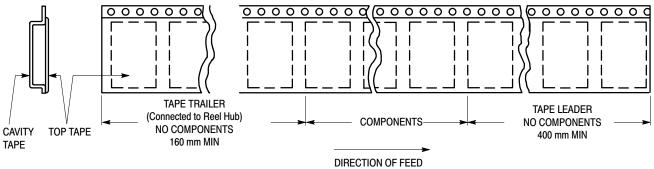
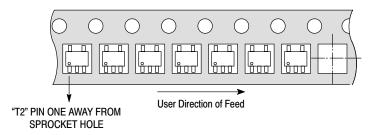
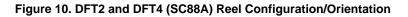


Figure 9. Tape Ends for Finished Goods





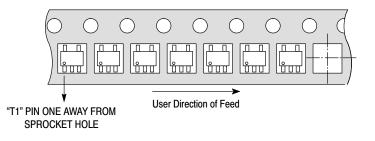
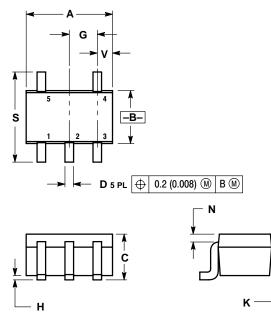


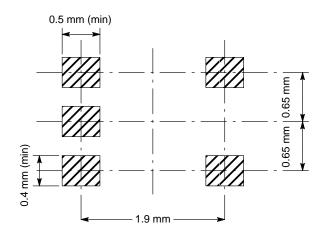
Figure 11. DTT1 and DTT3 (TSOP5) Reel Configuration/Orientation

PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 ISSUE B



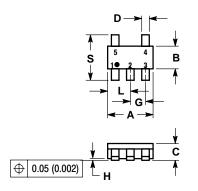
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	INC	INCHES MILLIMETERS						
DIM	MIN	MAX	MIN	MAX				
Α	0.071	0.087	1.80	2.20				
В	0.045	0.053	1.15	1.35				
C	0.031	0.043	0.80	1.10				
D	0.004	0.012	0.10	0.30				
G	0.026	BSC	0.65	BSC				
н		0.004		0.10				
J	0.004	0.010	0.10	0.25				
K	0.004	0.012	0.10	0.30				
Ν	0.008	REF	0.20	REF				
S	0.079	0.087	2.00	2.20				
٧	0.012	0.016	0.30	0.40	1			



PACKAGE DIMENSIONS

TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE CASE 483-01 ISSUE A

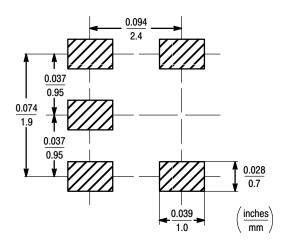
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NOTES:

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
ſ	0.10	0.26	0.0040	0.0102
Κ	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0°	10 °
S	2.50	3.00	0.0985	0.1181



<u>Notes</u>

<u>Notes</u>

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